# Reactivity of Metal Oxalate EUV Resists as a Function of the Central Metal

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# **EUV Lithography**



### **EUV** Lithography

- Photons liberate electrons in the resist and possibly cause chemistry to occur in the process
- Further Chemistry due to electron-resist interactions

### **Resist chemistry can be improved by:**

- Increasing the number of photons absorbed
- Efficient reactivity of secondary electrons

#### References

<sup>1</sup>T. Kozawa and S. Tagawa, Jpn. J. Appl.Phys., 49 (3) (2010) 030001. <sup>2</sup>A. Narasimhan, S. Grzeskowiak, et al., Proc. SPIE, 9779 (2016) 97790F. <sup>3</sup>J. Torok, et al., J. Photopolym. Sci. and Technol., 26 (5) (2013) 625–634. <sup>4</sup>P. de Schepper, et al., Proc. SPIE, **9425** (2015) 942507. <sup>5</sup>T. H. Fedynyshyn, et al., *Proc. SPIE*, **5039** (2003) 310.

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## **Comparison of Metal Centers Previous Work**





E<sub>size</sub> = 70 mJ/cm<sup>2</sup>

- Number of d electrons = 3
- Oxidation State = (III)
- \*Calculated EUV abs. = 5.8 μm<sup>-1</sup>

#### $E_{size} = 48 \text{ mJ/cm}^2$

- Number of d electrons = 5
- Oxidation State = (III)
- \*Calculated EUV abs. = 6.0 μm<sup>-1</sup>

### Improved Sensitivity

### 35 nm h/p lines

\*Calculated values are based on CXRO absorption using an assumed film density of 1.5 g/cm<sup>3</sup>

<sup>7</sup>M. Marnell, et al., "*A Molecular Inorganic Approach to EUV Photoresists*", presented at SPIE advanced lithography conference, (February 2014), San Jose, CA.

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#### E<sub>size</sub> = 27 mJ/cm<sup>2</sup>

- Number of d electrons = 6
- Oxidation State = (III)
- \*Calculated EUV abs. = 6.1 μm<sup>-1</sup>

## **EUV Atomic Absorption**

### **Atomic Absorption Cross Section per mole**



nm 13.5  $\sigma_{\alpha}$  [cm<sup>2</sup>/mol] at

## **EUV Absorption Measurements**



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# **EUV Absorption Experimental Design**

- Measure relative transmission at identical times to avoid pulse to pulse variations.
- Resist thicknesses on the membrane are measured using a J. A. Woollam M-2000 fixed angle ellipsometer equipped with Complete Ease software.

= Si<sub>3</sub>N<sub>4</sub> Membrane + Material

### **Top Down View of Photodiodes**





### **EUV Absorption Measurements**



# **EUV Linear Absorption Coefficients**



- Comparing the three metal oxalates (NP1, NP3, and NP4), there is only a small change in EUV absorption.
- Consequently, there must be very different reactivities to account for the change in sensitivity.

 Traditional photoresists have abs. coefficient of typically 5 um<sup>-1</sup>.

\*EUV linear absorption coefficients for NP3 and NP4 are based on the measured value of NP1 and the CXRO database.

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### Molecular Organometallic Resists for EUV (MORE): Cobalt Compound (NP1)

Current understanding of photo-mechanism:





Acta Crystallographica, Section E: Structure Reports Online **65** (10) (2009).

- Upon Exposure to EUV light or electrons CO<sub>2</sub> is generated and outgassed from the resist.
- The photoproduct, Co(II)(bpy)(ox), is a coordination polymer that polymerizes through bridging oxalate ligands.
- This bridging occurs when one of the oxalate ligands is eliminated as CO<sub>2</sub>

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Co(II)(bpy)(ox)

## E<sub>size</sub> vs. Metal Center Redox Potential



Literature Values<sup>8-12</sup>

There appears to be a correlation between the reducibility of the metal and  $E_{size}$ .

Hypothesis: There may be a correlation between reducibility of the metal and  $CO_2$  outgassing based upon the photo-mechanism.

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## **Outgassing Spectrum of NP1 (electrons)**



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Relative Intensity (AU)

### **Outgassing Spectra (electrons)**

![](_page_11_Figure_1.jpeg)

# CO<sub>2</sub> Outgassing Signal NP4: 80 eV Electrons

![](_page_12_Figure_1.jpeg)

### **CO<sub>2</sub> Liberated per Incident Electron: 80 eV**

![](_page_13_Figure_1.jpeg)

## **CO<sub>2</sub> Liberated per Incident Electron: 80 eV**

![](_page_14_Figure_1.jpeg)

## **CO<sub>2</sub> Outgassing vs. Electron Energy**

![](_page_15_Figure_1.jpeg)

## **CO<sub>2</sub> Liberated per Absorbed EUV Photon**

![](_page_16_Figure_1.jpeg)

# **CO<sub>2</sub> Outgassing vs. Metal Reducibility**

![](_page_17_Figure_1.jpeg)

- More easily reduced molecule outgasses more CO<sub>2</sub>.
- This could explain the change in E<sub>size</sub> when varying the central metal.

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# Conclusions

![](_page_18_Figure_1.jpeg)

- Between the three photoresists, a small change in EUV absorption does not account for the large change in E<sub>size</sub>.
- Based upon our understanding of the photo-mechanism increased CO<sub>2</sub> outgassing should improve sensitivity.
- The rate of CO<sub>2</sub> outgassing seems to be correlated to the reducibility of the central metal.

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